







SN74HCS32 ZHCSKQ8C - JANUARY 2020 - REVISED DECEMBER 2021

SN74HCS32 具有施密特触发输入的四路 2 输入或门

1 特性

- 宽工作电压范围: 2V 至 6V
- 施密特触发输入可实现慢速或高噪声输入信号
- 低功耗
 - I_{CC} 典型值为 100nA
 - 输入泄漏电流典型值为 ±100nA
- 电压为 6V 时,输出驱动为 ±7.8mA
- 工作环境温度范围: 40°C 至 +125°C, TA

2 应用

- 通过更少的输入来监控误差信号
- 将低电平有效使能信号相结合

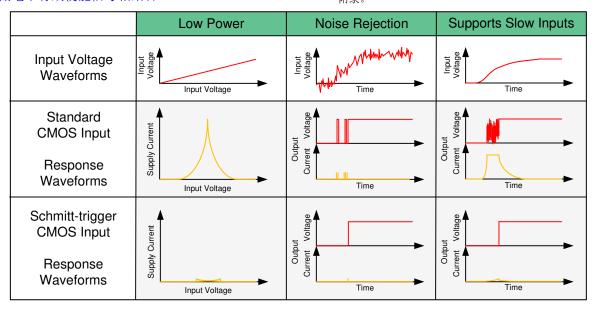
3 说明

此器件包含四个具有施密特触发输入的独立双输入或 门。每个逻辑门以正逻辑执行布尔函数 Y = A + B。

器件信息

HH I I I I I I I I I I I I I I I I I I							
器件型号	封装⁽¹⁾	封装尺寸(标称值)					
SN74HCS32PW	TSSOP (14)	5.00mm × 4.40mm					
SN74HCS32D	SOIC (14)	9.90mm × 3.90mm					
SN74HCS32BQA	WQFN (14)	3.00mm × 2.50mm					
SN74HCS32DYY	SOT-23-THIN (14)	2.00 mm x 4.20 mm					

如需了解所有可用封装,请参阅产品说明书末尾的可订购产品 附录。



施密特触发输入的优势



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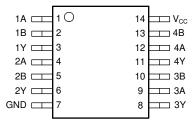
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4 Revision History 注:以前版本的页码可能与当前版本的页码不同

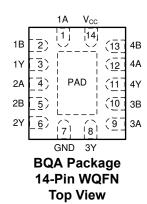
Changes from Revision B (January 2021) to Revision C (December 2021)	Page
• 向 <i>器件信息</i> 添加了 DYY 封装信息	1
Added DYY package to Pin Configurations and Functions	3
Added DYY package to Thermal Information table	5
Changes from Revision A (May 2020) to Revision B (January 2021)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式	
• 向 <i>器件信息</i> 添加了 BQA 封装信息	1
Added BQA package to Thermal Information table	5
Changes from Revision * (January 2020) to Revision A (May 2020)	Page
• 向 <i>器件信息</i> 添加了 D 封装信息	
Added D package column to Thermal Information table	5



5 Pin Configuration and Functions



D, PW or DYY Package SOIC, TSSOP or SOT Top View



PIN		1/0	DESCRIPTION
NAME	NO.	_ 1/0	DESCRIPTION
1A	1	Input	Channel 1, Input A
1B	2	Input	Channel 1, Input B
1Y	3	Output	Channel 1, Output Y
2A	4	Input	Channel 2, Input A
2B	5	Input	Channel 2, Input B
2Y	6	Output	Channel 2, Output Y
GND	7	_	Ground
3Y	8	Output	Channel 3, Output Y
3A	9	Input	Channel 3, Input A
3B	10	Input	Channel 3, Input B
4Y	11	Output	Channel 4, Output Y
4A	12	Input	Channel 4, Input A
4B	13	Input	Channel 4, Input B
V _{CC}	14	_	Positive Supply
Thermal Pad	(1)	_	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply

(1) BQA Package only.



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		- 0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		±20	mA
I _{OK}	Output clamp current ⁽²⁾	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		±20	mA
Io	Continuous output current	V _O = 0 to V _{CC}		±35	mA
	Continuous current through V _{CC} or GND			±70	mA
TJ	Junction temperature ⁽³⁾			150	°C
T _{stg}	Storage temperature		- 65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) Assured by design.

6.2 ESD Ratings

			VALUE	UNIT
V		Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±4000	V
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per ANSI/ESDA/ JEDEC JS-002 ⁽²⁾	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	2	5	6	V
VI	Input voltage	0		V _{CC}	V
Vo	Output voltage	0		V _{CC}	V
∆ t/ ∆ v	Input transition rise and fall rate		Ur	nlimited	ns/V
T _A	Ambient temperature	- 40		125	°C

Product Folder Links: SN74HCS32

6.4 Thermal Information

			SN74HCS32					
	THERMAL METRIC(1)	PW (TSSOP)	D (SOIC)	BQA (WQFN)	DYY (SOT)	UNIT		
		14 PINS	14 PINS	14 PINS	14 PINS			
R _{θ JA}	Junction-to-ambient thermal resistance	151.7	133.6	109.7	236.5	°C/W		
R _θ JC(top)	Junction-to-case (top) thermal resistance	79.4	89.0	111.0	143.2	°C/W		
R _{θ JB}	Junction-to-board thermal resistance	94.7	89.5	77.9	146.0	°C/W		
ΨЈТ	Junction-to-top characterization parameter	25.2	45.5	20.2	29.5	°C/W		
Ψ_{JB}	Junction-to-board characterization parameter	94.1	89.1	77.8	145.6	°C/W		
R _θ JC(bot)	Junction-to-case (bottom) thermal resistance	N/A	N/A	56.6	N/A	°C/W		

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over operating free-air temperature range; typical ratings measured at TA = 25°C (unless otherwise noted).

	PARAMETER	TEST CO	NDITIONS	V _{cc}	MIN	TYP	MAX	UNIT
				2 V	0.7		1.5	
V_{T+}	Positive switching threshold			4.5 V	1.7		3.15	V
				6 V	2.1		4.2	
				2 V	0.3		1.0	
V_{T-}	Negative switching threshold			4.5 V	0.9		2.2	V
				6 V	1.2		3.0	1
				2 V	0.2		1.0	
ΔV_T	Hysteresis (V _{T+} - V _{T-})			4.5 V	0.4		1.4	V
				6 V	0.6		1.6	
			I _{OH} = -20 μA	2 V to 6 V	V _{CC} - 0.1	V _{CC} - 0.002		
V_{OH}	High-level output voltage	$V_I = V_{IH}$ or V_{IL}	I _{OH} = -6 mA	4.5 V	4.0	4.3		V
			I _{OH} = -7.8 mA	6 V	5.4	5.75		
			I _{OL} = 20 μA	2 V to 6 V		0.002	0.1	
V_{OL}	Low-level output voltage	$V_I = V_{IH}$ or V_{IL}	I _{OL} = 6 mA	4.5 V		0.18	0.30	V
			I _{OL} = 7.8 mA	6 V		0.22	0.33	1
l _l	Input leakage current	$V_I = V_{CC}$ or 0		6 V		±100	±1000	nA
I _{CC}	Supply current	$V_I = V_{CC}$ or 0, I_C	_D = 0	6 V		0.1	2	μA
Ci	Input capacitance			2 V to 6 V			5	pF
C _{pd}	Power dissipation capacitance per gate	No load		2 V to 6 V		10		pF



6.6 Switching Characteristics

 C_L = 50 pF; over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See *Parameter Measurement Information*

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	MIN	TYP	MAX	UNIT
				2 V		15	36	
t _{pd}	t _{pd} Propagation delay	A or B	Υ	4.5 V		7	13	ns
				6 V		6	12	
			Y	2 V		9	16	
t _t Transition-time	Transition-time			4.5 V		5	9	ns
				6 V		4	8	

6.7 Typical Characteristics

 $T_A = 25^{\circ}C$

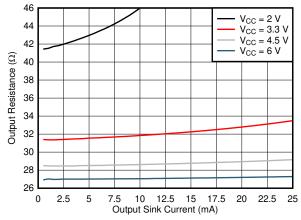


图 6-1. Output driver resistance in LOW state.

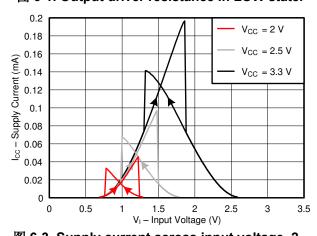


图 6-3. Supply current across input voltage, 2-, 2.5-, and 3.3-V supply

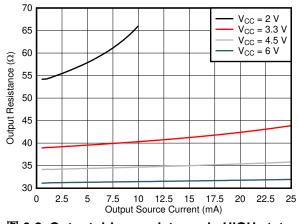


图 6-2. Output driver resistance in HIGH state.

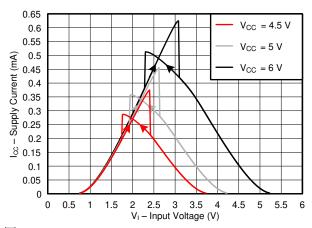


图 6-4. Supply current across input voltage, 4.5-, 5-, and 6-V supply

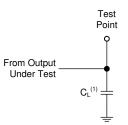
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7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_t < 2.5 ns.

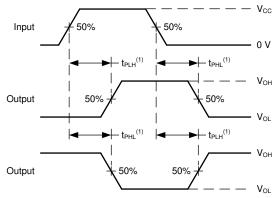
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



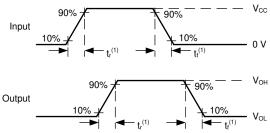
(1) C_L includes probe and test-fixture capacitance.

图 7-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .

图 7-2. Voltage Waveforms Propagation Delays



(1) The greater between t_{r} and t_{f} is the same as t_{t} .

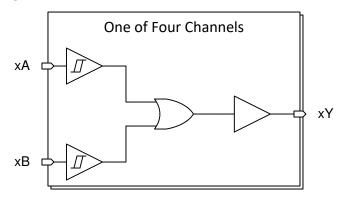
图 7-3. Voltage Waveforms, Input and Output Transition Times

8 Detailed Description

8.1 Overview

This device contains four independent 2-input OR Gates with Schmitt-trigger inputs. Each gate performs the Boolean function Y = A + B in positive logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.2 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see Understanding Schmitt Triggers.

8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Electrical Placement of Clamping Diodes for Each Input and Output.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

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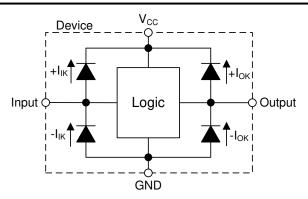


图 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

表 8-1. Function Table

INP	UTS	OUTPUT
Α	В	Y
L	L	L
Н	Х	Н
X	н	Н

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围, TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计,以确保系统功能。

9.1 Application Information

In this application, three 2-input OR gates are combined to produce a 4-input OR gate function as shown in Typical application block diagram. The fourth gate can be used for another application in the system, or the inputs can be grounded and the channel left unused.

The SN74HCS32 is used to directly control the Enable pin of a fan driver. The fan driver requires only one input signal to be HIGH before being enabled, and should be disabled in the event that all signals go LOW. The 4-input OR gate function combines the four individual overheat signals into a single active-high enable signal.

Temperature sensors can often be spread throughout a system rather than being in a centralized location. This would mean longer length traces or wires to pass signals through leading to slower edge transitions. This makes the SN74HCS32 ideal for the application since it has Schmitt-trigger inputs that do not have input transition rate requirements.

9.2 Typical Application

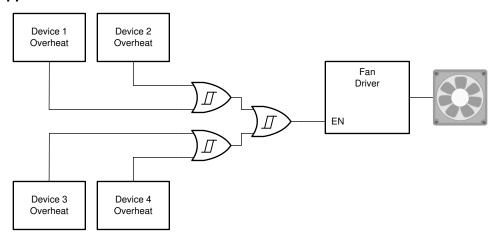


图 9-1. Typical application block diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCS32 plus the maximum static supply current, I_{CC} , listed in *Electrical Characteristics* and any transient current required for switching. The logic device can only source as much current as is provided by the positive supply source. Be sure not to exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS32 plus the maximum supply current, I_{CC}, listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

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The SN74HCS32 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

The SN74HCS32 can drive a load with total resistance described by $R_L \ge V_O$ / I_O , with the output voltage and current defined in the Electrical Characteristics table with V_{OH} and V_{OL}. When outputting in the high state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and Cpd Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, T_{J(max)} listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the Absolute Maximum Ratings. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the Absolute Maximum Ratings.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCS32, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The SN74HCS32 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical* Characteristics. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the VOH specification in the Electrical Characteristics. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to Feature Description section for additional information regarding the outputs for this device.

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9.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
- 2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS32 to the receiving device(s).
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)})$ Ω . This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
- 4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation.

9.2.3 Application Curves

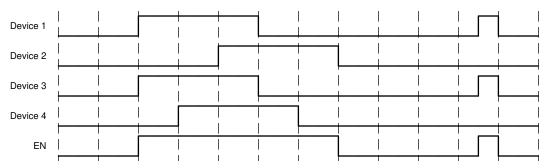


图 9-2. Application timing diagram

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10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

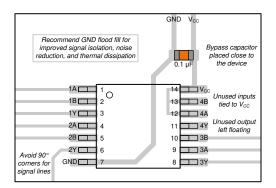


图 11-1. Example layout for the SN74HCS32



12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, HCMOS Design Considerations application report (SCLA007)
- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report (SDYA009)
- Texas Instruments, Designing With Logic application report

12.2 接收文档更新通知

要接收文档更新通知,请导航至 ti.com 上的器件产品文件夹。点击*订阅更新* 进行注册,即可每周接收产品信息更改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

12.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料,可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者"按原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI 的《使用条款》。

12.4 Trademarks

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12.5 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序,可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级,大至整个器件故障。精密的集成电路可能更容易受到损坏,这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.6 术语表

TI术语表本术语表列出并解释了术语、首字母缩略词和定义。



13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
SN74HCS32BQAR	Active	Production	WQFN (BQA) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS32
SN74HCS32BQAR.A	Active	Production	WQFN (BQA) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS32
SN74HCS32DR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HCS32
SN74HCS32DR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS32
SN74HCS32DR.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	-	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS32
SN74HCS32DYYR	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS32
SN74HCS32DYYR.A	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS32
SN74HCS32PWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HCS32
SN74HCS32PWR.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS32
SN74HCS32PWR.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	-	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS32

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

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OTHER QUALIFIED VERSIONS OF SN74HCS32:

Automotive: SN74HCS32-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS32BQAR	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1
SN74HCS32DR	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HCS32DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HCS32DYYR	SOT-23- THIN	DYY	14	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
SN74HCS32PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCS32BQAR	WQFN	BQA	14	3000	210.0	185.0	35.0
SN74HCS32DR	SOIC	D	14	2500	366.0	364.0	50.0
SN74HCS32DR	SOIC	D	14	2500	353.0	353.0	32.0
SN74HCS32DYYR	SOT-23-THIN	DYY	14	3000	336.6	336.6	31.8
SN74HCS32PWR	TSSOP	PW	14	2000	356.0	356.0	35.0

PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side
- This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- 5. Reference JEDEC Registration MO-345, Variation AB



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



2.5 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



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PLASTIC QUAD FLAT PACK-NO LEAD



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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